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PATENT
5500-36100/TT2823

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Gardner, et al.

Serial No. 09/207,972

Filed: December 9, 1998

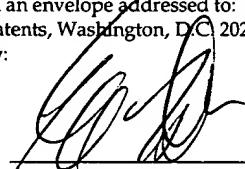
For: **ULTRATHIN HIGH-K GATE
DIELECTRIC WITH FAVORABLE
INTERFACE PROPERTIES FOR
IMPROVED SEMICONDUCTOR
DEVICE PERFORMANCE**

§ Group Art Unit: 2815
§ Examiner: Warren, M.
§
§ Atty. Dkt. No. 5500-36100

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I hereby certify that this correspondence is being
deposited with the U.S. Postal Service with sufficient postage
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date indicated below:

August 9, 2001
Date


Kevin L. Daffer

AMENDMENT; RESPONSE TO OFFICE ACTION MAILED MAY 9, 2001

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir/Madam:

This paper is submitted in response to the Office Action of May 9, 2001 to further
highlight why the application is in condition for allowance.

Please amend the case as listed below.

In the Claims:

Please add the following claims:

30. (Added) The device as recited in claim 16, wherein said high-K dielectric has a low-trap-density.

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